CHAPTER 8

Semiconductor Nanowires for Electronic and Optoelectronic Device Applications

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CONTENTS

1. Introduction 279
2. Synthesis of Semiconductor Nanowires 280
    2.1. Catalytic Methods via Vapor-Liquid-Solid Growth Mechanism . . 280
    2.2. Non-Catalytic Methods 287
3. Characterization of Semiconductor Nanowires 289
    3.1. Transport Properties 290
    3.2. Phonon-Transport Properties 291
    3.3. Optical Properties 291
4. Device Application of Semiconductor Nanowires 294
    4.1. Electronic Devices 294
    4.2. Quantum Devices 295
    4.3. Light Emitting Devices 297
    4.4. Photoconductivity and Optical Switching Devices 301
    4.5. Sensors 303
    4.6. Field Emission Applications 303
    4.7. Photovoltaic Applications 305
5. Assembly and Integration 306
6. Conclusions 307
References 308

1. INTRODUCTION

With the discovery of carbon nanotubes in 1991 [1], nanoscale materials have attracted tremendous interest and attention over the past decade for their vast areas of applications ranging from electronics to pharmaceuticals. Nanostructures are defined as having dimension between 1 to 100 nm. One-dimensional (1D) nanostructures such as nanowires, nanobelts

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